OPA8709

Infrared LED Chip

High Speed / N Side-Up

GaAlAs/GaAlAs

1. Material

Substrate GaAlAs (P Type) Removed
Epitaxial Layer GaAlAs (N/P Type)

2. Electrode

N(Cathode) Side Gold Alloy
P(Anode) Side Gold Alloy

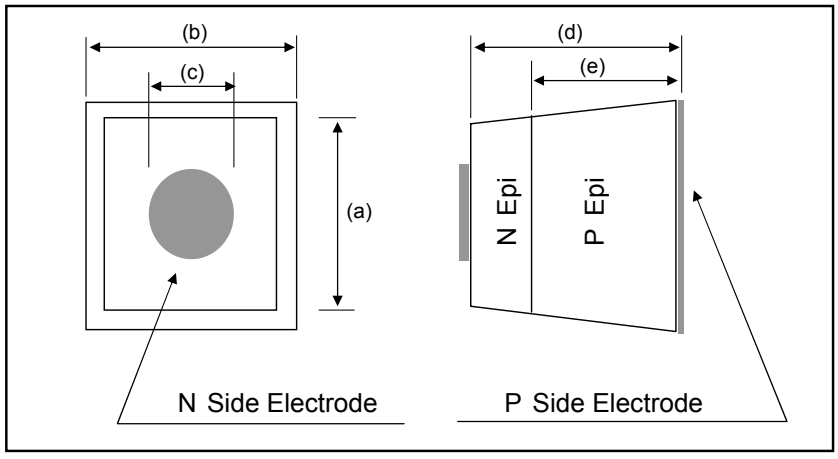
3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_{F(1)}$		1.1		V	IF=10uA
	$V_{F(2)}$		1.75	1.9	V	IF=50mA
Reverse Voltage	V_R	5			V	IR=10uA
Power	P_O	6.5	9.5		mW	IF=50mA
Wavelength	λ_P		878		nm	IF=50mA
	$\Delta\lambda$		45		nm	IF=50mA
Rise Time	Tr		28		ns	
Fall Time	Tf		18		ns	

※ Note : Power is measured by Sorter E/T system with bare chip.

4. Mechanical Data

(a) Emission Area ---------- 8.1mil x 8.1mil
(b) Bottom Area ---------- 9.1mil x 9.1mil
(c) Bonding Pad ---------- 150um
(d) Chip Thickness ---------- 8mil
(e) Junction Height ---------- 3.5mil



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